

C<sup>1</sup>  
cont.

a plurality of second semiconductor regions of the second conductivity type having a second depth as measured from said major surface of the body region that is less than the first depth,

wherein the body region is exposed between the plurality of second semiconductor regions and the second semiconductor regions connect the plurality of first semiconductor regions spaced apart from one another.

C<sup>2</sup>

13. (Twice Amended) A process for producing a semiconductor device comprising:

forming a body region of a first conductivity type in a semiconductor substrate, the body region having a major surface opposite to a surface shared between the semiconductor substrate and the body region;

forming a plurality of trench gates extending through the body region;

forming a plurality of first semiconductor regions of a second conductivity type that is different from the first conductivity type, the first semiconductor regions having a first depth as measured from said major surface of the body region, at least a portion of the first semiconductor regions flanking the trench gates on both of their sides and being in contact with said trench gates via films bordering and insulating the trench gates;

forming a plurality of second semiconductor regions of the second conductivity type having a second depth as measured from said major surface of the body region that is less than the first depth; and

connecting the plurality of first semiconductor regions spaced apart from one another by the second semiconductor regions;

wherein the body region is exposed between the plurality of second semiconductor regions.

**Please see the attached Appendix for the changes made to effect the above claims.**